

KVR800D2D4F5/4GEF 4GB 512M x 72-Bit PC2-6400 CL5 ECC 240-Pin FBDIMM

Description:

This document describes ValueRAM's 4GB (512M x 72-bit) PC2-6400 CL5 SDRAM (Synchronous DRAM) "fully buffered" ECC "dual rank" memory module. This module is based on thirty-six 256M x 4-bit 800MHz DDR2 FBGA components. The module also includes an AMB device (Advanced Memory Buffer). The electrical and mechanical specifications are as follows:

Feature:

- FBDIMM Module: 240-pin
- JEDEC Standard: R/C H or E
- Memory Organization: 2 rank of x4 devices
- DDR2 DRAM Interface: SSTL_18
- DDR2 Speed Grade: 800 Mbps
- CAS Latency: 5-5-5
- Module Bandwidth: 6.4 GB/s
- DRAM: VDD = VDDQ = 1.8V
- AMB: VCC = VCCFBD = 1.5V
- EEPROM: VDDSPD = 3.3V (typical)
- Heat Spreader: Full DIMM Heat Spreader (FDHS)
- PCB Height: 30.35mm, double-side
- RoHS Compliant

DRAM Supported:

Elpida F-die

DDR2 240-pin FBDIMM Pinout:

Pin #	Front Side	Pin #	Back Side	Pin #	Front Side	Pin #	Back Side	Pin #	Front Side	Pin #	Back Side	Pin #	Front Side	Pin #	Back Side
1	V _{DD}	121	V _{DD}	31	PN3	151	SN3	61	PN9	181	SN9	91	PS9	211	SS9
2	V _{DD}	122	V _{DD}	32	PN3	152	SN3	62	V _{SS}	182	V _{SS}	92	V _{SS}	212	V _{SS}
3	V _{DD}	123	V _{DD}	33	V _{SS}	153	V _{SS}	63	PN10	183	SN10	93	PS5	213	SS5
4	V _{SS}	124	V _{SS}	34	PN4	154	SN4	64	PN10	184	SN10	94	PS5	214	SS5
5	V _{DD}	125	V _{DD}	35	PN4	155	SN4	65	V _{SS}	185	V _{SS}	95	V _{SS}	215	V _{SS}
6	V _{DD}	126	V _{DD}	36	V _{SS}	156	V _{SS}	66	PN11	186	SN11	96	PS6	216	SS6
7	V _{DD}	127	V _{DD}	37	PN5	157	SN5	67	PN11	187	SN11	97	PS6	217	SS6
8	V _{SS}	128	V _{SS}	38	PN5	158	SN5	68	V _{SS}	188	V _{SS}	98	V _{SS}	218	V _{SS}
9	V _{CC}	129	V _{CC}	39	V _{SS}	159	V _{SS}	KEY				99	PS7	219	SS7
10	V _{CC}	130	V _{CC}	40	PN13	160	SN13	69	V _{SS}	189	V _{SS}	100	PS7	220	SS7
11	V _{SS}	131	V _{SS}	41	PN13	161	SN13	70	PS0	190	SS0	101	V _{SS}	221	V _{SS}
12	V _{CC}	132	V _{CC}	42	V _{SS}	162	V _{SS}	71	PS0	191	SS0	102	PS8	222	SS8
13	V _{CC}	133	V _{CC}	43	V _{SS}	163	V _{SS}	72	V _{SS}	192	V _{SS}	103	PS8	223	SS8
14	V _{SS}	134	V _{SS}	44	RFU*	164	RFU*	73	PS1	193	SS1	104	V _{SS}	224	V _{SS}
15	V _{TT}	135	V _{TT}	45	RFU*	165	RFU*	74	PS1	194	SS1	105	RFU**	225	RFU**
16	VID1	136	VID0	46	V _{SS}	166	V _{SS}	75	V _{SS}	195	V _{SS}	106	RFU**	226	RFU**
17	RESET	137	DNU/M_Test	47	V _{SS}	167	V _{SS}	76	PS2	196	SS2	107	V _{SS}	227	V _{SS}
18	V _{SS}	138	V _{SS}	48	PN12	168	SN12	77	PS2	197	SS2	108	V _{DD}	228	SCK
19	RFU**	139	RFU**	49	PN12	169	SN12	78	V _{SS}	198	V _{SS}	109	V _{DD}	229	SCK
20	RFU**	140	RFU**	50	V _{SS}	170	V _{SS}	79	PS3	199	SS3	110	V _{SS}	230	V _{SS}
21	V _{SS}	141	V _{SS}	51	PN6	171	SN6	80	PS3	200	SS3	111	V _{DD}	231	V _{DD}
22	PN0	142	SN0	52	PN6	172	SN6	81	V _{SS}	201	V _{SS}	112	V _{DD}	232	V _{DD}
23	PN0	143	SN0	53	V _{SS}	173	V _{SS}	82	PS4	202	SS4	113	V _{DD}	233	V _{DD}
24	V _{SS}	144	V _{SS}	54	PN7	174	SN7	83	PS4	203	SS4	114	V _{SS}	234	V _{SS}
25	PN1	145	SN1	55	PN7	175	SN7	84	V _{SS}	204	V _{SS}	115	V _{DD}	235	V _{DD}
26	PN1	146	SN1	56	V _{SS}	176	V _{SS}	85	V _{SS}	205	V _{SS}	116	V _{DD}	236	V _{DD}
27	V _{SS}	147	V _{SS}	57	PN8	177	SN8	86	RFU*	206	RFU*	117	V _{TT}	237	V _{TT}
28	PN2	148	SN2	58	PN8	178	SN8	87	RFU*	207	RFU*	118	SA2	238	VDDSPD
29	PN2	149	SN2	59	V _{SS}	179	V _{SS}	88	V _{SS}	208	V _{SS}	119	SDA	239	SA0
30	V _{SS}	150	V _{SS}	60	PN9	180	SN9	89	V _{SS}	209	V _{SS}	120	SCL	240	SA1
								90	PS9	210	SS9				

RFU = Reserved Future Use.

* These pin positions are reserved for forwarded clocks to be used in future module implementations

** These pin positions are reserved for future architecture flexibility

1) The following signals are CRC bits and thus appear out of the normal sequence: PN12/PN12, SN12/SN12, PN13/PN13, SN13/SN13, PS9/PS9, SS9/SS9

DIMM Connector Pin Description:

Pin Name	Pin Description	Count
SCK	System Clock Input, positive line ¹	1
$\overline{\text{SCK}}$	System Clock Input, negative line ¹	1
PN[13:0]	Primary Northbound Data, positive lines	14
$\overline{\text{PN}}[13:0]$	Primary Northbound Data, negative lines	14
PS[9:0]	Primary Southbound Data, positive lines	10
$\overline{\text{PS}}[9:0]$	Primary Southbound Data, negative lines	10
SN[13:0]	Secondary Northbound Data, positive lines	14
$\overline{\text{SN}}[13:0]$	Secondary Northbound Data, negative lines	14
SS[9:0]	Secondary Southbound Data, positive lines	10
$\overline{\text{SS}}[9:0]$	Secondary Southbound Data, negative lines	10
SCL	Serial Presence Detect (SPD) Clock Input	1
SDA	SPD Data Input / Output	1
SA[2:0]	SPD Address Inputs, also used to select the DIMM number in the AMB	3
VID[1:0]	Voltage ID: These pins must be unconnected for DDR2-based Fully Buffered DIMMs VID[0] is V_{DD} value: OPEN = 1.8 V, GND = 1.5 V; VID[1] is V_{CC} value: OPEN = 1.5 V, GND = 1.2 V	2
$\overline{\text{RESET}}$	AMB reset signal	1
RFU	Reserved for Future Use ²	16
V_{CC}	AMB Core Power and AMB Channel Interface Power (1.5 Volt)	8
V_{DD}	DRAM Power and AMB DRAM I/O Power (1.8 Volt)	24
V_{TT}	DRAM Address/Command/Clock Termination Power ($V_{DD}/2$)	4
V_{DDSPD}	SPD Power	1
V_{SS}	Ground	80
DNU/M_Test	The DNU/M_Test pin provides an external connection on R/Cs A-D for testing the margin of Vref which is produced by a voltage divider on the module. It is not intended to be used in normal system operation and must not be connected (DNU) in a system. This test pin may have other features on future card designs and if it does, will be included in this specification at that time. 1	1
	Total	240

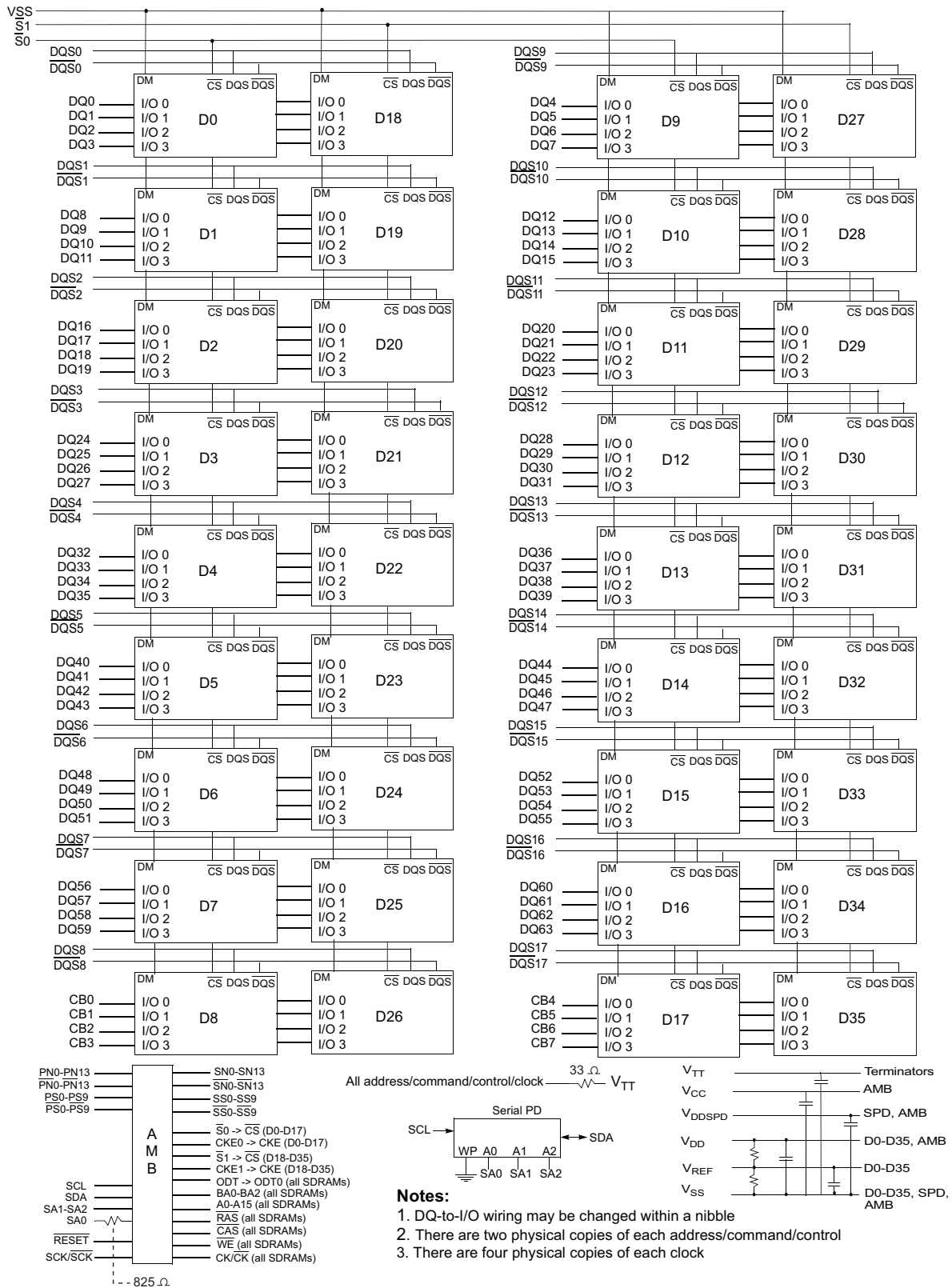
1. System Clock Signals SCK and $\overline{\text{SCK}}$ switch at one half the DRAM CK/ $\overline{\text{CK}}$ frequency
2. Eight pins reserved for forwarded clocks, eight pins reserved for future architecture flexibility

Absolute Maximum Ratings

Symbol	Parameter	MIN	MAX	Units
VIN, VOUT	Voltage on any pin relative to V_{SS}	-0.3	1.75	V
VCC	Voltage on V_{CC} pin relative to V_{SS}	-0.3	1.75	V
VDD	Voltage V_{DD} pin relative to V_{SS}	-0.5	2.3	V
VTT	Voltage on V_{TT} pin relative to V_{SS}	-0.5	2.3	V
T_{STG}	Storage temperature	-55	100	°C
T_{CASE}	DDR2 SDRAM device operating temperature (Ambient)	0	95 ⁽¹⁾	°C
	AMB device operating temperature (Ambient)	0	110	°C

Note: (1) Above 85°C DRAM case temperature the Auto-Refresh command interval has to be reduced to tREFI = 3.9 μ s.

Functional Block Diagram:



Architecture:

Advanced Memory Buffer Pin Description:

Pin Name	Pin Description	Count
FB-DIMM Channel Signals		99
SCK	System Clock Input, positive line	1
$\overline{\text{SCK}}$	System Clock Input, negative line	1
PN[13:0]	Primary Northbound Data, positive lines	14
$\overline{\text{PN}}[13:0]$	Primary Northbound Data, negative lines	14
PS[9:0]	Primary Southbound Data, positive lines	10
$\overline{\text{PS}}[9:0]$	Primary Southbound Data, negative lines	10
SN[13:0]	Secondary Northbound Data, positive lines	14
$\overline{\text{SN}}[13:0]$	Secondary Northbound Data, negative lines	14
SS[9:0]	Secondary Southbound Data, positive lines	10
$\overline{\text{SS}}[9:0]$	Secondary Southbound Data, negative lines	10
FBDRES	To an external precision calibration resistor connected to Vcc	1
DDR2 Interface Signals		175
DQS[8:0]	Data Strobes, positive lines	9
$\overline{\text{DQS}}[8:0]$	Data Strobes, negative lines	9
DQS[17:9]/DM[8:0]	Data Strobes (x4 DRAM only), positive lines. These signals are driven low to x8 DRAM on writes.	9
$\overline{\text{DQS}}[17:9]$	Data Strobes (x4 DRAM only), negative lines	9
DQ[63:0]	Data	64
CB[7:0]	Checkbits	8
A[15:0]A, A[15:0]B	Addresses. A10 is part of the pre-charge command	32
BA[2:0]A, BA[2:0]B	Bank Addresses	6
$\overline{\text{RASA}}$, $\overline{\text{RASB}}$	Part of command, with $\overline{\text{CAS}}$, $\overline{\text{WE}}$, and $\overline{\text{CS}}[1:0]$.	2
$\overline{\text{CASA}}$, $\overline{\text{CASB}}$	Part of command, with $\overline{\text{RAS}}$, $\overline{\text{WE}}$, and $\overline{\text{CS}}[1:0]$.	2
$\overline{\text{WEA}}$, $\overline{\text{WEB}}$	Part of command, with $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, and $\overline{\text{CS}}[1:0]$.	2
ODTA, ODTB	On-die Termination Enable	2
CKE[1:0]A, CKE[1:0]B	Clock Enable (one per rank)	4
$\overline{\text{CS}}[1:0]A$, $\overline{\text{CS}}[1:0]B$	Chip Select (one per rank)	4
CLK[3:0]	CLK[1:0] used on 9 and 18 device DIMMs, CLK[3:0] used on 36 device DIMMs. CLK[3:2] should be output disabled when not in use.	4
$\overline{\text{CLK}}[3:0]$	Negative lines for CLK[3:0]	4
DDRC_C14	DDR Compensation: Common return pin for DDRC_B18 and DDRC_C18.	1
DDRC_B18	DDR Compensation: Resistor connected to common return pin DDRC_C14	1
DDRC_C18	DDR Compensation: Resistor connected to common return pin DDRC_C14	1
DDRC_B12	DDR Compensation: Resistor connected to V _{SS}	1
DDRC_C12	DDR Compensation: Resistor connected to V _{DD}	1

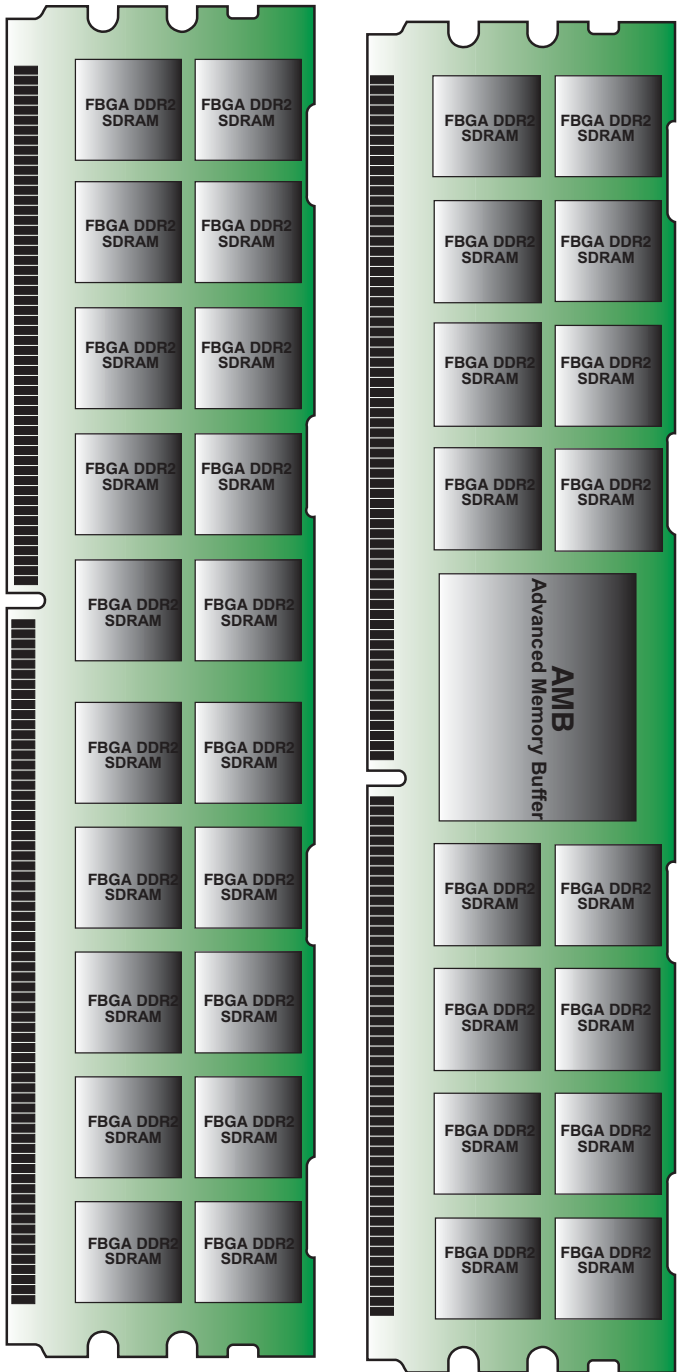
Advanced Memory Buffer Pin Description:

SPD Bus Interface Signals		5
SCL	Serial Presence Detect (SPD) Clock Input	1
SDA	SPD Data Input / Output	1
SA[2:0]	SPD Address Inputs, also used to select the DIMM number in the AMB	3
Miscellaneous Signals		163
PLLTSTO	PLL Clock Observability Output	1
VCCAPLL	Analog VCC for the PLL. Tied with low pass filter to VCC.	1
VSSAPLL	Analog VSS for the PLL. Tied to ground on the AMB die. Do not tie to ground on the DIMM.	1
TEST_pin#	Leave floating on the DIMM	6
TESTLO_pin#	Tie to ground on the DIMM ²	5
BFUNC	Tie to ground to set functionality as "buffer on DIMM."	1
$\overline{\text{RESET}}$	AMB reset signal	1
NC	No connect. Many NC are connected to VDD on the DIMM, to lower the impedance of the VDD power islands.	129
RFU	Reserved for Future Use	18
Power/Ground Signals		213
V _{CC}	AMB Core Power (1.5 Volt)	24
V _{CCFBD}	AMB Channel I/O Power (1.5 Volt)	8
V _{DD}	AMB DRAM I/O Power (1.8 Volt)	24
V _{DDSPD}	SPD Power (3.3 Volt)	1
V _{SS}	Ground	156
Total		655

1. System Clock Signals SCK and $\overline{\text{SCK}}$ switch at one half the DRAM CK/ $\overline{\text{CK}}$ frequency.

2. TESTLO_AB20 and TESTLO_AC20 should be configured for debug purposes on prototype DIMMs: each pin should have a zero ohm resistor pulldown to ground, and an unpopulated resistor pullup to VCC. These resistors can be replaced on production DIMMs with a direct connection to ground.

Package Dimensions:



(Units = millimeters)

